

# TPCA8102

Lithium Ion Battery Applications  
 Notebook PC Applications  
 Portable Equipment Applications

- Small footprint due to small and thin package
- Low drain-source ON resistance:  $R_{DS(ON)} = 4.5m\Omega$  (typ.)
- High forward transfer admittance:  $|Y_{fs}| = 60S$  (typ.)
- Low leakage current:  $I_{DSS} = -10 \mu A$  (max) ( $V_{DS} = -30 V$ )
- Enhancement mode:  $V_{th} = -0.8$  to  $-2.0 V$  ( $V_{DS} = -10 V, I_D = -1 mA$ )

### Absolute Maximum Ratings (Ta = 25°C)

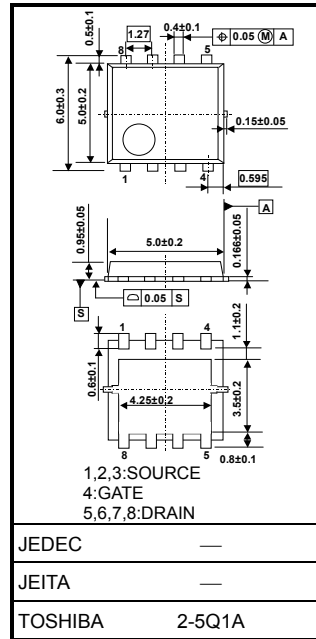
Characteristics	Symbol	Rating	Unit
Drain-source voltage	$V_{DSS}$	-30	V
Drain-gate voltage ( $R_{GS} = 20 k\Omega$ )	$V_{DGR}$	-30	V
Gate-source voltage	$V_{GSS}$	$\pm 20$	V
Drain current	DC (Note 1)	$I_D$	-40
	Pulsed (Note 1)	$I_{DP}$	-120
Drain power dissipation ( $T_c=25^\circ C$ )	$P_D$	45	W
Drain power dissipation ( $t = 10 s$ ) (Note 2a)	$P_D$	2.8	W
Drain power dissipation ( $t = 10 s$ ) (Note 2b)	$P_D$	1.6	W
Single pulse avalanche energy (Note 3)	$E_{AS}$	208	mJ
Avalanche current	$I_{AR}$	-40	A
Repetitive avalanche energy ( $T_c=25^\circ C$ ) (Note 4)	$E_{AR}$	4.5	mJ
Channel temperature	$T_{ch}$	150	°C
Storage temperature range	$T_{stg}$	-55 to 150	°C

Note: For Notes 1 to 4, refer to the next page.

Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings. Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/Derating Concept and Methods) and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

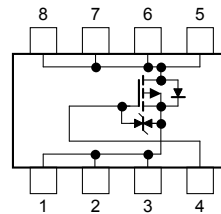
This transistor is an electrostatic-sensitive device.  
 Please handle with caution.

Unit: mm



Weight: 0.076 g (typ.)

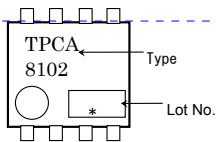
### Circuit Configuration



Thermal Characteristics

Characteristics	Symbol	Max	Unit
Thermal resistance, channel to case ( $T_c=25^\circ\text{C}$ )	$R_{th(ch-c)}$	2.78	$^\circ\text{C/W}$
Thermal resistance, channel to ambient ( $t = 10\text{ s}$ ) (Note 2a)	$R_{th(ch-a)}$	44.6	$^\circ\text{C/W}$
Thermal resistance, channel to ambient ( $t = 10\text{ s}$ ) (Note 2b)	$R_{th(ch-a)}$	78.1	$^\circ\text{C/W}$

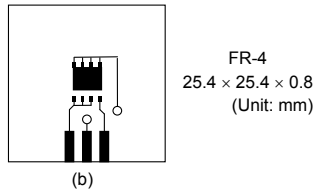
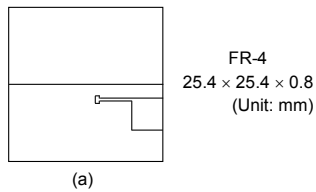
Marking (Note 5)



**コメント [H1]:** \*は和文フォントです。英文 TD には使用しないでください。日本語フォントが入っていない PC で見ると文字化けが起こります。

Note 1: Ensure that the channel temperature does not exceed  $150^\circ\text{C}$ .

Note 2: (a) Device mounted on a glass-epoxy board (a) (b) Device mounted on a glass-epoxy board (b)

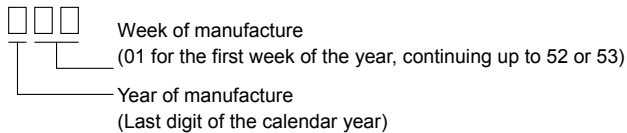


Note 3:  $V_{DD} = 24\text{ V}$ ,  $T_{ch} = 25^\circ\text{C}$  (initial),  $L = 100\ \mu\text{H}$ ,  $R_G = 25\ \Omega$ ,  $I_{AR} = -40\text{ A}$

Note 4: Repetitive rating: pulse width limited by max channel temperature

Note 5: "O" on the lower left of the marking indicates Pin 1.

\* Weekly code (three digits):



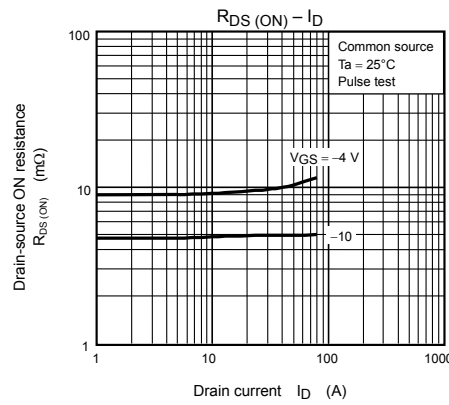
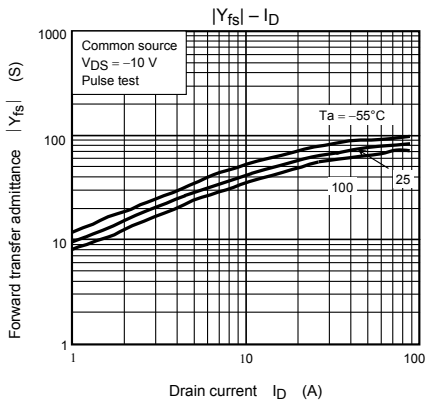
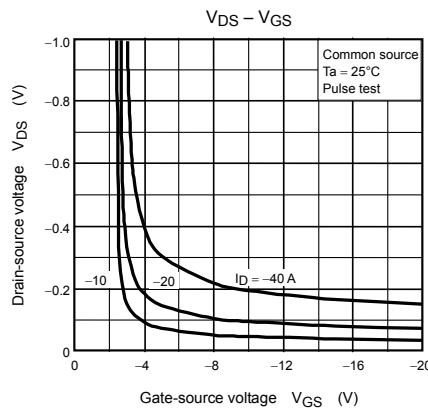
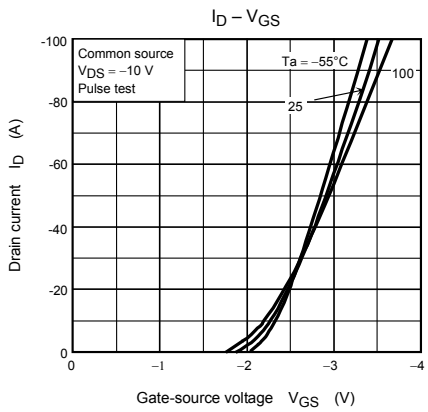
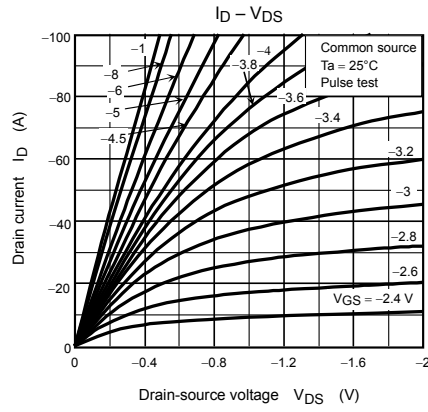
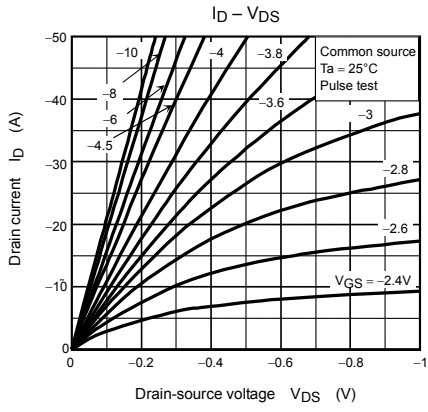
**Electrical Characteristics (Ta = 25°C)**

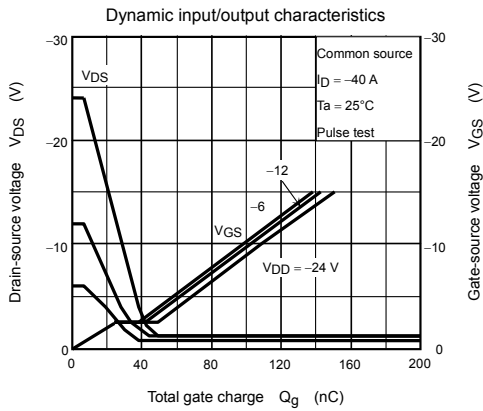
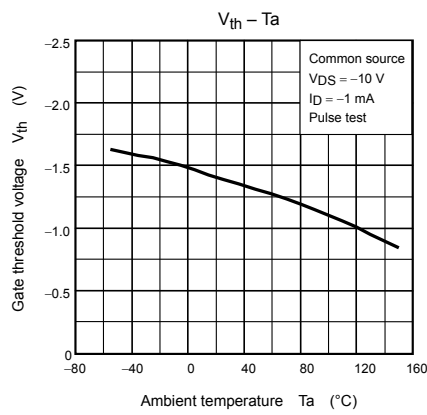
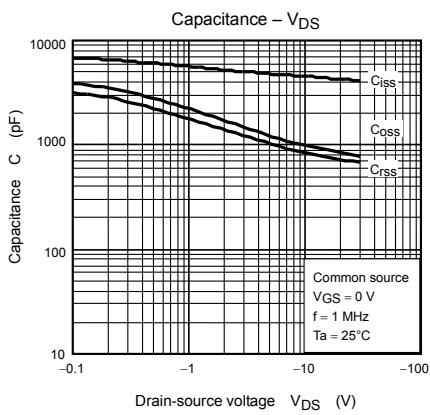
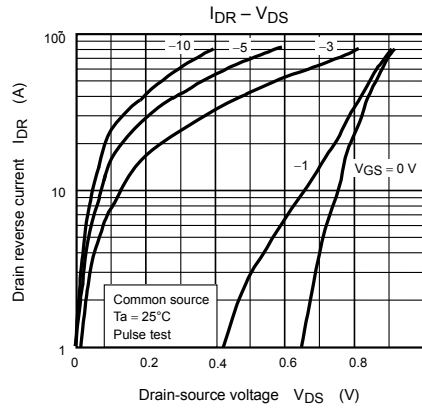
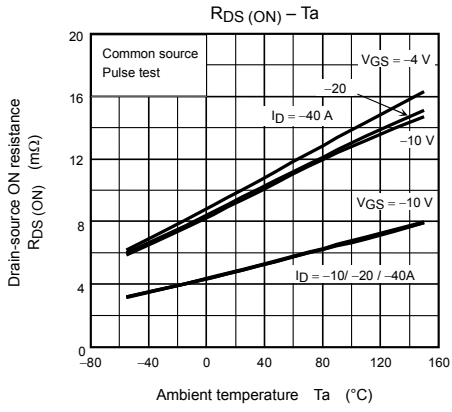
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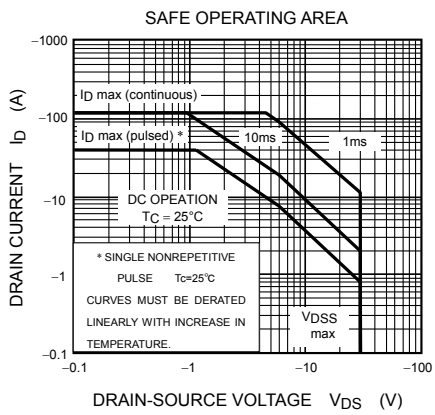
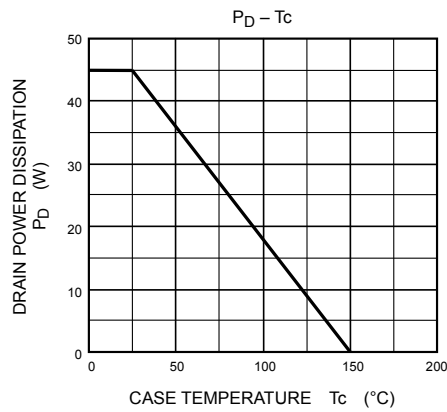
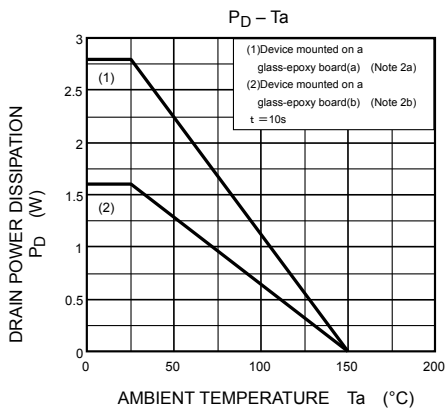
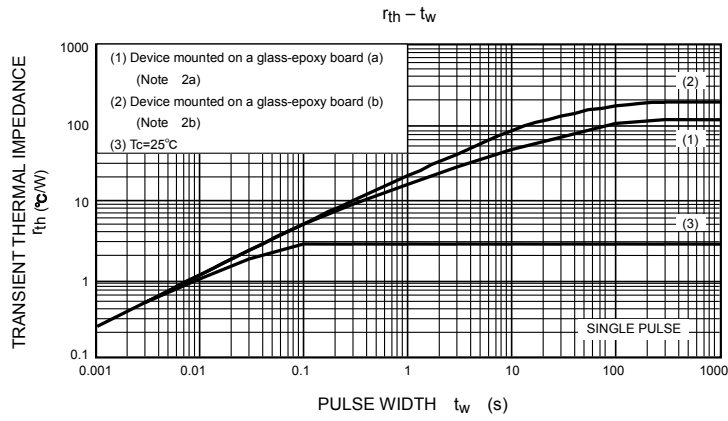
Characteristics		Symbol	Test Condition	Min	Typ.	Max	Unit
Gate leakage current		$I_{GSS}$	$V_{GS} = \pm 16\text{ V}, V_{DS} = 0\text{ V}$	—	—	$\pm 10$	$\mu\text{A}$
Drain cut-OFF current		$I_{DSS}$	$V_{DS} = -30\text{ V}, V_{GS} = 0\text{ V}$	—	—	-10	$\mu\text{A}$
Drain-source breakdown voltage		$V_{(BR)DSS}$	$I_D = -10\text{ mA}, V_{GS} = 0\text{ V}$	-30	—	—	V
		$V_{(BR)DSX}$	$I_D = -10\text{ mA}, V_{GS} = 20\text{ V}$	-15	—	—	
Gate threshold voltage		$V_{th}$	$V_{DS} = -10\text{ V}, I_D = -1\text{ mA}$	-0.8	—	-2.0	V
Drain-source ON resistance		$R_{DS(ON)}$	$V_{GS} = -4\text{ V}, I_D = -20\text{ A}$	—	9.0	14	$\text{m}\Omega$
			$V_{GS} = -10\text{ V}, I_D = -20\text{ A}$	—	4.5	6.0	
Forward transfer admittance		$ Y_{fs} $	$V_{DS} = -10\text{ V}, I_D = -20\text{ A}$	30	60	—	S
Input capacitance		$C_{iss}$	$V_{DS} = -10\text{ V}, V_{GS} = 0\text{ V}, f = 1\text{ MHz}$	—	4600	—	pF
Reverse transfer capacitance		$C_{rSS}$		—	850	—	
Output capacitance		$C_{oss}$		—	980	—	
Switching time	Rise time	$t_r$		—	10	—	ns
	Turn-ON time	$t_{on}$		—	20	—	
	Fall time	$t_f$		—	78	—	
	Turn-OFF time	$t_{off}$		Duty $\leq 1\%$ , $t_w = 10\ \mu\text{s}$	—	220	
Total gate charge (gate-source plus gate-drain)		$Q_g$	$V_{DD} \approx -24\text{ V}, V_{GS} = 10\text{ V}, I_D = -40\text{ A}$	—	109	—	nC
Gate-source charge 1		$Q_{gs1}$		—	24	—	
Gate-drain ("miller") charge		$Q_{gd}$		—	25	—	

**Source-Drain Ratings and Characteristics (Ta = 25°C)**

Characteristics		Symbol	Test Condition	Min	Typ.	Max	Unit
Drain reverse current	Pulse (Note 1)	$I_{DRP}$	—	—	—	-120	A
Forward voltage (diode)		$V_{DSF}$	$I_{DR} = -40\text{ A}, V_{GS} = 0\text{ V}$	—	—	1.2	V







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